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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/653,281	08/31/2000	Kevin L. Beaman	M4065.0278/P27899-0818	4745	
75	590 12/17/2003		EXAMI	NER	
Thomas J D'Amico			BOOTH, RICHARD A		
Dickstein Shapi 2101 L Street N	iro Morin & Oshinsky LL IW	P	ART UNIT PAPER NUMBER		
Washington, D	C 20037-1526		2812		
			DATE MAILED: 12/17/2003	į.	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	w/C			
Office Assiss Suprement	09/653,281	BEAMAN ET AL.				
Office Action Summary	Examiner	Art Unit				
	Richard A. Booth	2812				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address P riod for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  Estencions of time may be available under the provisions of 3 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (8) MCNTHS from the mailing date of this communication.  If the period for reply septide above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  If NO period for reply septide above is how them thirty (30) days are poly within the statutory benefit of the septide above is less than thirty (30) days will be good to reply villable to each of or reply villable the set or adended period for reply villable the set or adended period for reply villable the set or adended period for reply villable the set. Sc. § 133).  Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent from adjustment. See 3 CFR 1.704(b)						
Status						
1) Responsive to communication(s) filed on <u>26 November 2003</u> .						
2a) This action is FINAL. 2b) This action is non-final.						
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
4) ⊠ Claim(s) 1-3, 6-14, 16, 18, 21-29, 31, and 35-4a) Of the above claim(s) is/are withdramus)	wn from consideration.	n.				
Application Papers						
9) The specification is objected to by the Examiner.  10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.  Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to . See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. §§ 119 and 120						
12)  Acknowledgment is made of a claim for foreign a)  All b) Some * (○) None of:  1.  Certified copies of the priority document 2.  Certified copies of the priority document 3.  Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list 13)  Acknowledgment is made of a claim for domest since a specific reference was included in the fir 37 CFR 1.78. a)  The translation of the foreign language pro	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)). of the certified copies not receive ic priority under 35 U.S.C. § 119(s st sentence of the specification or posisional application has been receive in the specification or positional application has been received.	on No  bd in this Nationa  bd.  c) (to a provisiona  in an Application  eived.	al application) n Data Sheet.			
reference was included in the first sentence of the						

Notice of References Cited (PTO-892)
 Notice of Draftsperson's Patent Drawing Review (PTO-948)
 Information Disclosure Statement(s) (PTO-1449) Paper No(s)

Attachment(s)

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#### DETAILED ACTION

#### Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 11/26/03 has been entered.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-3, 6-16, 18, 21-31, and 34-45 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al., U.S. Patent 6,376,309 in view of Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" or Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method".

Wang et al. shows the invention as claimed including forming a tunnel oxide 404 on a substrate 402; forming a first conductor 406 over the tunnel oxide 404; forming an insulating layer 410 over the first conductor layer, the insulating layer comprising a first oxide layer over the first conductor layer, a nitride layer over the first oxide layer, and a

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second oxide layer over the nitride layer, wherein the second oxide layer is formed by oxidizing said nitride layer to a thickness of fifty angstroms (see column 3, lines 39-54); forming a second conductor layer 412 over the insulating layer; etching at least the first conductor layer, the second conductor layer, and the insulating layer, thereby defining at least one stacked structure (see Figure 3).

Note with regard to claims 6, 21, and 36, the hydrogen and oxygen present when forming the second oxide layer will react to form steam.

Wang et al. fails to show forming the second oxide layer using an oxidizing ambient in atomic oxygen to form the oxide layer with a thickness of 60% of a targeted thickness and at various temperatures and times.

Both Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" and Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method" disclose forming an oxide layer in a microwave environment using an oxidizing method with atomic oxygen (see abstracts of both methods). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Wang et al. so as to form the second oxide layer using the process taught by Hoff et al. or Ruzyllo et al. because both of these processes allow for oxide growth at low temperatures with high breakdown values.

With respect to the particular time and temperature of the oxidation, it would have been obvious to determine through routine experimentation the optimum time and temperature to conduct the oxidation process based upon a variety of factors including

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the desired thermal budget and would not lend patentability to the instant application absent the showing of unexpected results.

### Response to Arguments

Applicant's arguments have been fully considered but they are not persuasive (see advisory action mailed 11/19/03).

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is (571) 272-1668. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 308-1782.

Primard A. Blooth Primary Examiner Art Unit 2812